



# FHD030

## NPN Silicon Darlington High Power Transistor



### Features:

1. Using triple-diffusion process.High output current. Small driving power.
2. Highest amplification factor. High inverse voltage.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for current output,voltage adjustment and servo circuit of numerical control machine.
5. Quality Class: JP, JT, JCT, GS, G, G+

### TECHNICAL DATA:

( $T_a = 25^{\circ}\text{C}$ )

Parameter name	Symbols	Unit	Specifications										Test Condition
			A	B	C	D	E	F	G	H	I	J	
Collector-Emitter Voltage	$V_{CEO}$	V	100	200	300	400	500	600	700	800	900	1000	
Emitter-Base Voltage	$V_{EBO}$	V	5										
Max. Collector Current	$I_{CM}$	A	2.0										
Max. Collector Dissipation	$P_{CM}$	W	30										$T_c:75^{\circ}\text{C}$
Junction Temperature	$T_{jm}$	$^{\circ}\text{C}$	175										
Storage Temperature	$T_{stg}$	$^{\circ}\text{C}$	-55~+175										
Collector-Emitter Leakage Current	$I_{CEO}$	mA	Max.:1.0										$V_{CE}=100\text{V}$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:2.0										$I_c=1\text{A}, I_b=0.01\text{A}$
DC Current Gain	$h_{FE}$		Min.:500										$V_{CE}=10\text{V}, I_c=1\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	100	200	300	400	500	600	700	800	900	1000	$I_c=5\text{mA}$
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	5										$I_E=20\text{mA}$

### Outline and Dimensions: